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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HM62V16100I Series

Wide Temperature Range Version
16 M SRAM (1-Mword × 16-bit)

ADE-203-1249C(Z)
Preliminary
Rev. 0.3
Mar. 13, 2003

Description

The Hitachi HM62V16100I Series is 16-Mbit static RAM organized 1-Mword × 16-bit. HM62V16100I Series has realized higher density, higher performance and low power consumption by employing CMOS process technology (6-transistor memory cell). It offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It has the package variations of 48-bump chip size package with 0.75 mm bump pitch and 48-pin plastic TSOPI for high density surface mounting.

Features

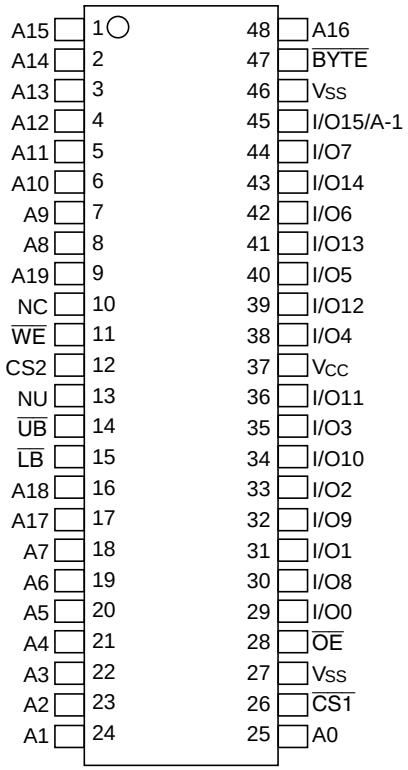
- Single 3.0 V supply: 2.7 V to 3.6 V
- Fast access time: 45/55 ns (max)
- Power dissipation:
  - Active: 9 mW/MHz (typ)
  - Standby: 1.5 µW (typ)
- Completely static memory.
  - No clock or timing strobe required
- Equal access and cycle times
- Common data input and output.
  - Three state output
- Battery backup operation.
  - 2 chip selection for battery backup
- Temperature range: –40 to +85°C

Ordering Information

Type No.	Access time	Package
HM62V16100LTI-4	45 ns	48-pin plastic TSOPI (normal-bend type) (TFP-48DA)
HM62V16100LTI-4SL	45 ns	
HM62V16100LTI-5	55 ns	
HM62V16100LTI-5SL	55 ns	
HM62V16100LBPI-4	45 ns	48-bump CSP with 0.75 mm bump pitch (TBP-48F)
HM62V16100LBPI-4SL	45 ns	
HM62V16100LBPI-5	55 ns	
HM62V16100LBPI-5SL	55 ns	

Pin Arrangement

48-pin TSOP



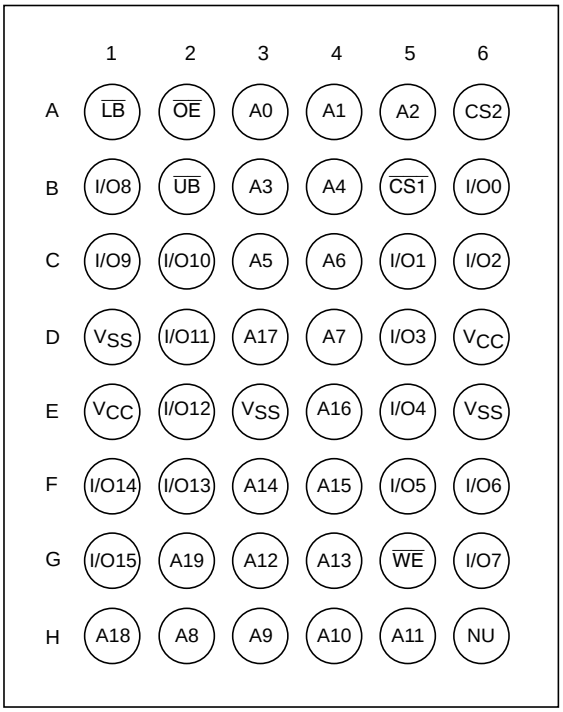
(Top view)

Pin Description (TSOP)

Pin name	Function
A0 to A19	Address input (word mode)
A-1 to A19	Address input (byte mode)
I/O0 to I/O15	Data input/output
$\overline{CS1}$	Chip select 1
CS2	Chip select 2
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
$\overline{LB}$	Lower byte select
$\overline{UB}$	Upper byte select
$\overline{BYTE}$	Byte enable
V_{CC}	Power supply
V_{SS}	Ground
NC	No connection
NU*[1]	Not used (test mode pin)

Note: 1. This pin should be connected to a ground (V_{SS}), or not be connected (open).

48-bumps CSP



(Top view)

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I/O0 to I/O15	Data input/output
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V_{CC}	Power supply
V_{SS}	Ground
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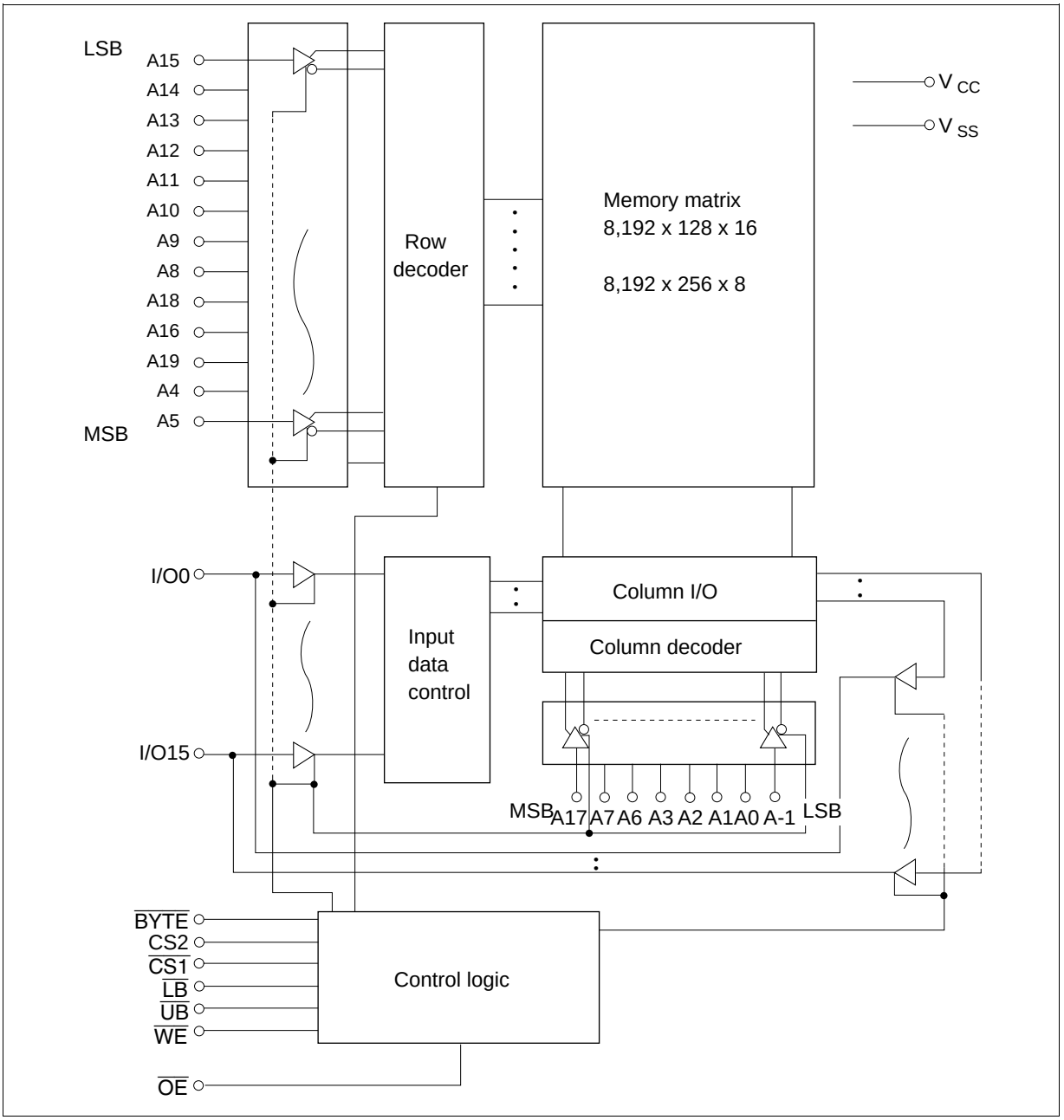
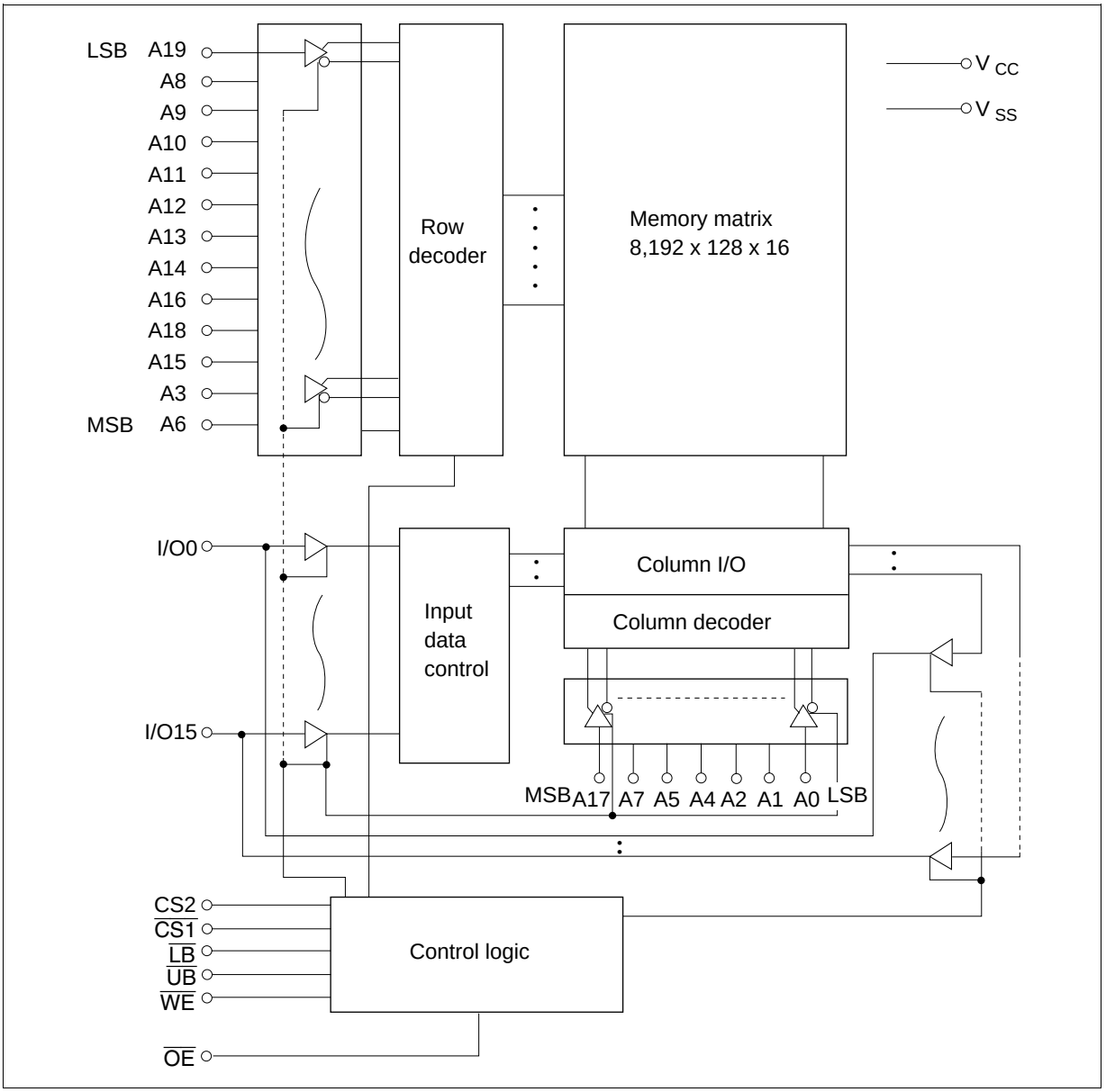
Note: 1. This pin should be connected to a ground (V_{SS}), or not be connected (open).

Block Diagram (TSOP)



Block Diagram (CSP)



Operation Table (TSOP)

Byte mode

$\overline{CS1}$	CS2	$\overline{WE}$	$\overline{OE}$	$\overline{UB}$	$\overline{LB}$	$\overline{BYTE}$	I/O0 to I/O7	I/O8 to I/O14	I/O15	Operation
H	×	×	×	×	×	L	High-Z	High-Z	High-Z	Standby
×	L	×	×	×	×	L	High-Z	High-Z	High-Z	Standby
L	H	H	L	×	×	L	Dout	High-Z	A-1	Read
L	H	L	×	×	×	L	Din	High-Z	A-1	Write
L	H	H	H	×	×	L	High-Z	High-Z	High-Z	Output disable

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Word mode

$\overline{CS1}$	CS2	$\overline{WE}$	$\overline{OE}$	$\overline{UB}$	$\overline{LB}$	$\overline{BYTE}$	I/O0 to I/O7	I/O8 to I/O14	I/O15	Operation
H	×	×	×	×	×	H	High-Z	High-Z	High-Z	Standby
×	L	×	×	×	×	H	High-Z	High-Z	High-Z	Standby
×	×	×	×	H	H	H	High-Z	High-Z	High-Z	Standby
L	H	H	L	L	L	H	Dout	Dout	Dout	Read
L	H	H	L	H	L	H	Dout	High-Z	High-Z	Lower byte read
L	H	H	L	L	H	H	High-Z	Dout	Dout	Upper byte read
L	H	L	×	L	L	H	Din	Din	Din	Write
L	H	L	×	H	L	H	Din	High-Z	High-Z	Lower byte write
L	H	L	×	L	H	H	High-Z	Din	Din	Upper byte write
L	H	H	H	×	×	H	High-Z	High-Z	High-Z	Output disable

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Operation Table (CSP)

$\overline{CS1}$	CS2	$\overline{WE}$	$\overline{OE}$	$\overline{UB}$	$\overline{LB}$	I/O0 to I/O7	I/O8 to I/O15	Operation
H	×	×	×	×	×	High-Z	High-Z	Standby
×	L	×	×	×	×	High-Z	High-Z	Standby
×	×	×	×	H	H	High-Z	High-Z	Standby
L	H	H	L	L	L	Dout	Dout	Read
L	H	H	L	H	L	Dout	High-Z	Lower byte read
L	H	H	L	L	H	High-Z	Dout	Upper byte read
L	H	L	×	L	L	Din	Din	Write
L	H	L	×	H	L	Din	High-Z	Lower byte write
L	H	L	×	L	H	High-Z	Din	Upper byte write
L	H	H	H	×	×	High-Z	High-Z	Output disable

Note: H: V_{IH}, L: V_{IL}, ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{CC}	–0.5 to + 4.6	V
Terminal voltage on any pin relative to V_{SS}	V_T	–0.5*[1] to V_{CC} + 0.3*[2]	V
Power dissipation	P_T	1.0	W
Storage temperature range	Tstg	–55 to +125	°C
Storage temperature range under bias	Tbias	–40 to +85	°C

Notes: 1. V_T min: –2.0 V for pulse half-width ≤ 10 ns.
2. Maximum voltage is +4.6 V.

DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	V_{CC}	2.7	3.0	3.6	V	
	V_{SS}	0	0	0	V	
Input high voltage	V_{IH}	2.2	—	V_{CC} + 0.3	V	
Input low voltage	V_{IL}	–0.3	—	0.6	V	1
Ambient temperature range	Ta	–40	—	85	°C	

Note: 1. V_{IL} min: –2.0 V for pulse half-width ≤ 10 ns.

DC Characteristics

Parameter	Symbol	Min	Typ*[1]	Max	Unit	Test conditions*[2]
Input leakage current	$\|I_{LI}\|$	—	—	1	µA	Vin = V_{SS} to V_{CC}
Output leakage current	$\|I_{LO}\|$	—	—	1	µA	$\overline{CS1}$ = V_{IH} or CS2 = V_{IL} or $\overline{OE}$ = V_{IH} or $\overline{WE}$ = V_{IL} or $\overline{LB}$ = $\overline{UB}$ = V_{IH}, $V_{I/O}$ = V_{SS} to V_{CC}
Operating current	I_{CC}	—	—	20	mA	$\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/ V_{IL}, $I_{I/O}$ = 0 mA
Average operating current	I_{CC1} (READ)	—	22	35	mA	Min. cycle, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, $\overline{WE}$ = V_{IH}, Others = V_{IH}/V_{IL}
	I_{CC1}	—	30	50	mA	Min. cycle, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/V_{IL}
	I_{CC2}*[5] (READ)	—	3	8	mA	Cycle time = 70 ns, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, $\overline{WE}$ = V_{IH}, Others = V_{IH}/V_{IL} Address increment scan or decrement scan
	I_{CC2}*[5]	—	20	30	mA	Cycle time = 70 ns, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS1}$ = V_{IL}, CS2 = V_{IH}, Others = V_{IH}/V_{IL} Address increment scan or decrement scan
	I_{CC3}	—	3	8	mA	Cycle time = 1 µs, duty = 100%, $I_{I/O}$ = 0 mA, $\overline{CS1}$ ≤ 0.2 V, CS2 ≥ V_{CC} – 0.2 V V_{IH} ≥ V_{CC} – 0.2 V, V_{IL} ≤ 0.2 V
Standby current	I_{SB}	—	0.1	0.5	mA	CS2 = V_{IL}
Standby current	I_{SB1}*[3]	—	0.5	25	µA	0 V ≤ Vin (1) 0 V ≤ CS2 ≤ 0.2 V or (2) $\overline{CS1}$ ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V or (3) $\overline{LB}$ = $\overline{UB}$ ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V, $\overline{CS1}$ ≤ 0.2 V Average value
	I_{SB1}*[4]	—	0.5	8	µA	
Output high voltage	V_{OH}	2.4	—	—	V	I_{OH} = –1 mA
	V_{OH}	V_{CC} – 0.2	—	—	V	I_{OH} = –100 µA
Output low voltage	V_{OL}	—	—	0.4	V	I_{OL} = 2 mA
	V_{OL}	—	—	0.2	V	I_{OL} = 100 µA

Notes: 1. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and not guaranteed.
2. $\overline{BYTE}$ pin supported by only TSOP type.
$\overline{BYTE} \geq V_{CC} - 0.2$ V or $\overline{BYTE} \leq 0.2$ V
3. This characteristic is guaranteed only for L-version.
4. This characteristic is guaranteed only for L-SL version.
5. I_{CC2} is the value measured while the valid address is increasing or decreasing by one bit.
Word mode: LSB (least significant bit) is A0.
Byte mode: LSB (least significant bit) is A-1.

Capacitance (Ta = +25°C, f = 1.0 MHz)

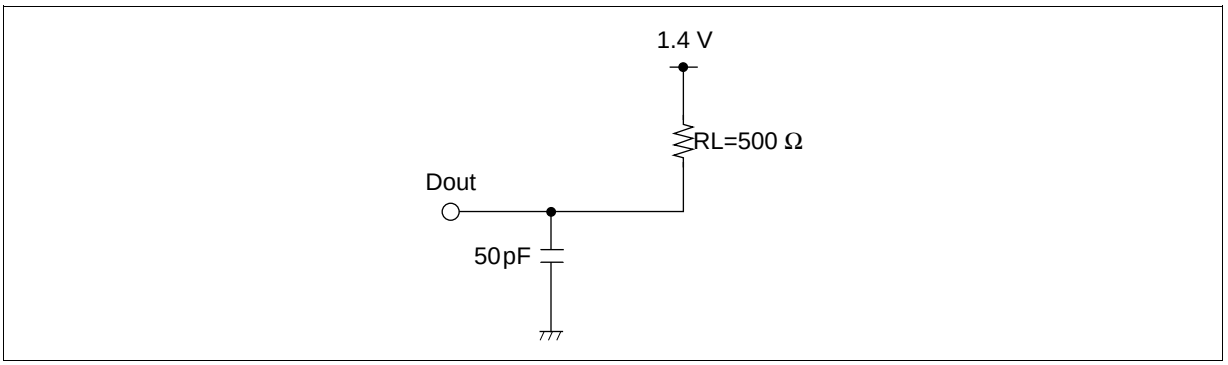
Parameter	Symbol	Min	Typ	Max	Unit	Test conditions	Note
Input capacitance	Cin	—	—	8	pF	Vin = 0 V	1
Input/output capacitance	$C_{I/O}$	—	—	10	pF	$V_{I/O}$ = 0 V	1

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = –40 to +85°C, V_{CC} = 2.7 V to 3.6 V, unless otherwise noted.)

Test Conditions

- Input pulse levels: V_{IL} = 0.4 V, V_{IH} = 2.4 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.4 V
- Output load: See figures (Including scope and jig)



Read Cycle

		HM62V16100I					
		-4		-5			
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Unit**	**Notes**
Read cycle time	t_{RC}	45	—	55	—	ns	
Address access time	t_{AA}	—	45	—	55	ns	
Chip select access time	t_{ACS1}	—	45	—	55	ns	
	t_{ACS2}	—	45	—	55	ns	
Output enable to output valid	t_{OE}	—	30	—	35	ns	
Output hold from address change	t_{OH}	10	—	10	—	ns	
$\overline{LB}$, $\overline{UB}$ access time	t_{BA}	—	45	—	55	ns	
Chip select to output in low-Z	t_{CLZ1}	10	—	10	—	ns	2, 3
	t_{CLZ2}	10	—	10	—	ns	2, 3
$\overline{LB}$, $\overline{UB}$ enable to low-Z	t_{BLZ}	5	—	5	—	ns	2, 3
Output enable to output in low-Z	t_{OLZ}	5	—	5	—	ns	2, 3
Chip deselect to output in high-Z	t_{CHZ1}	0	20	0	20	ns	1, 2, 3
	t_{CHZ2}	0	20	0	20	ns	1, 2, 3
$\overline{LB}$, $\overline{UB}$ disable to high-Z	t_{BHZ}	0	15	0	20	ns	1, 2, 3
Output disable to output in high-Z	t_{OHZ}	0	15	0	20	ns	1, 2, 3

Write Cycle

		HM62V16100I					
		-4		-5			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write cycle time	t_{WC}	45	—	55	—	ns	
Address valid to end of write	t_{AW}	45	—	50	—	ns	
Chip selection to end of write	t_{CW}	45	—	50	—	ns	5
Write pulse width	t_{WP}	35	—	40	—	ns	4
$\overline{LB}$, $\overline{UB}$ valid to end of write	t_{BW}	45	—	50	—	ns	
Address setup time	t_{AS}	0	—	0	—	ns	6
Write recovery time	t_{WR}	0	—	0	—	ns	7
Data to write time overlap	t_{DW}	25	—	25	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	ns	
Output active from end of write	t_{OW}	5	—	5	—	ns	2
Output disable to output in high-Z	t_{OHZ}	0	15	0	20	ns	1, 2
Write to output in high-Z	t_{WHZ}	0	15	0	20	ns	1, 2

Byte Control

		HM62V16100I					
		-4		-5			
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Unit**	**Notes**
$\overline{BYTE}$ setup time	t_{BS}	5	—	5	—	ms	8
$\overline{BYTE}$ recovery time	t_{BR}	5	—	5	—	ms	8

Notes: 1. t_{CHZ}, t_{OHZ}, t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

2. This parameter is sampled and not 100% tested.

3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.

4. A write occurs during the overlap of a low $\overline{CS1}$, a high CS2, a low $\overline{WE}$ and a low $\overline{LB}$ or a low $\overline{UB}$. A write begins at the latest transition among $\overline{CS1}$ going low, CS2 going high, $\overline{WE}$ going low and $\overline{LB}$ going low or $\overline{UB}$ going low. A write ends at the earliest transition among $\overline{CS1}$ going high, CS2 going low, $\overline{WE}$ going high and $\overline{LB}$ going high or $\overline{UB}$ going high. t_{WP} is measured from the beginning of write to the end of write.

5. t_{CW} is measured from the later of $\overline{CS1}$ going low or CS2 going high to the end of write.

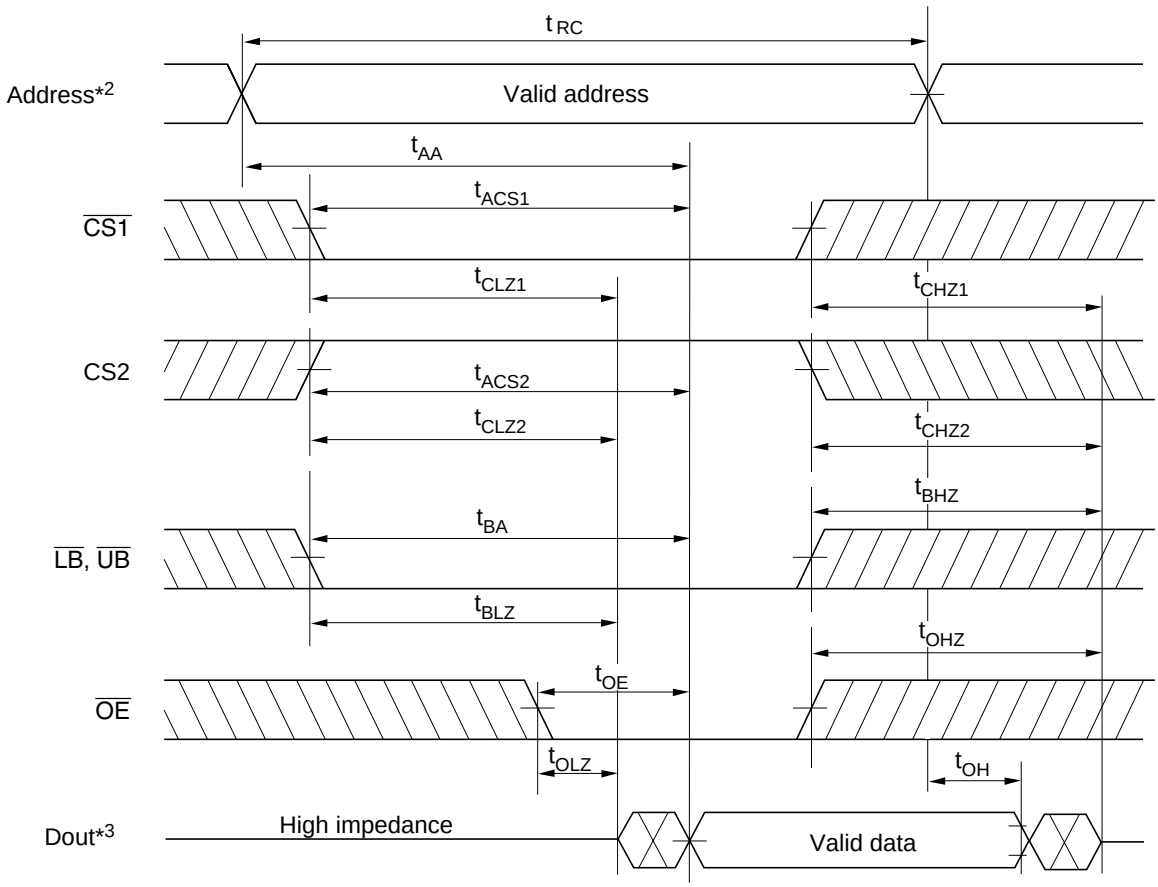
6. t_{AS} is measured from the address valid to the beginning of write.

7. t_{WR} is measured from the earliest of $\overline{CS1}$ or $\overline{WE}$ going high or CS2 going low to the end of write cycle.

8. Byte control supported by only TSOP type.

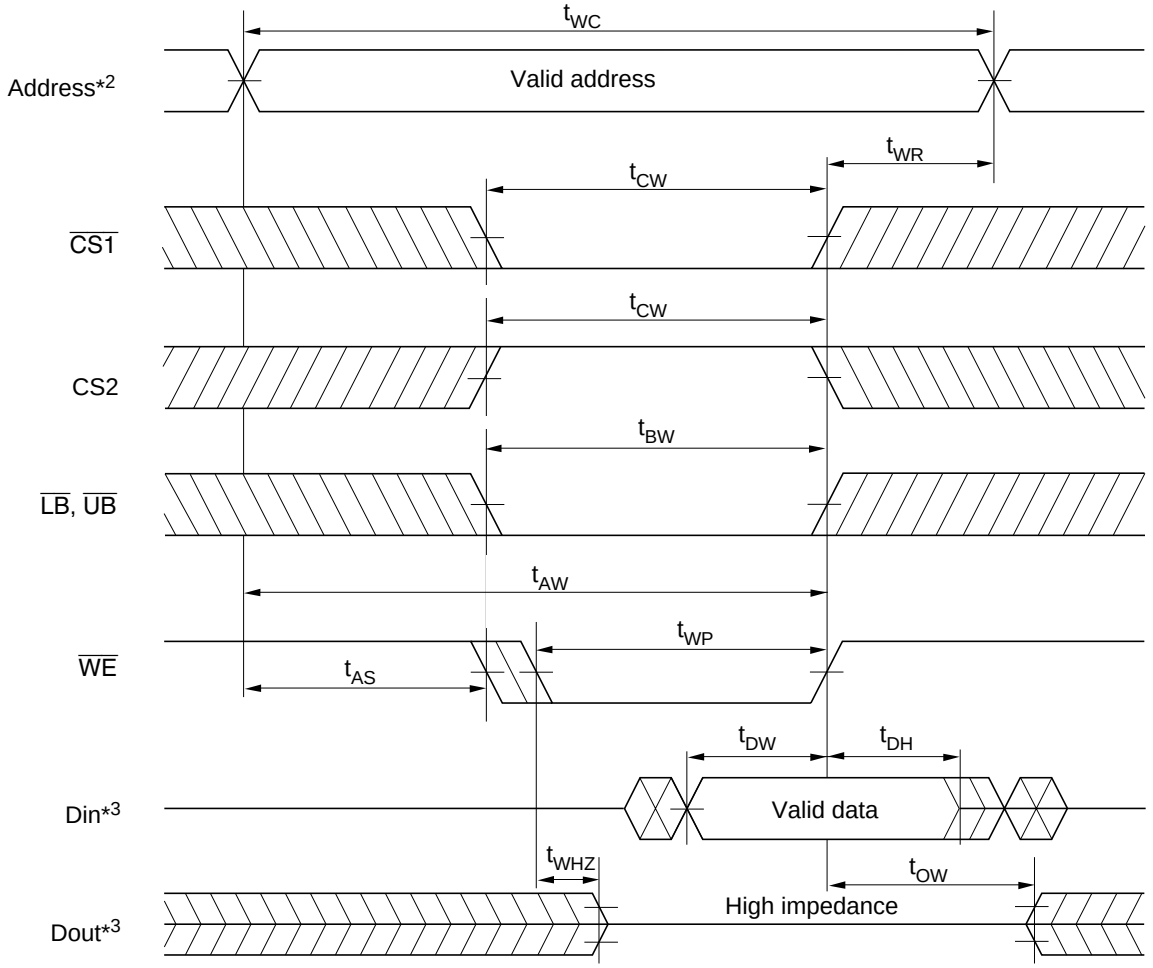
Timing Waveform

Read Cycle*1



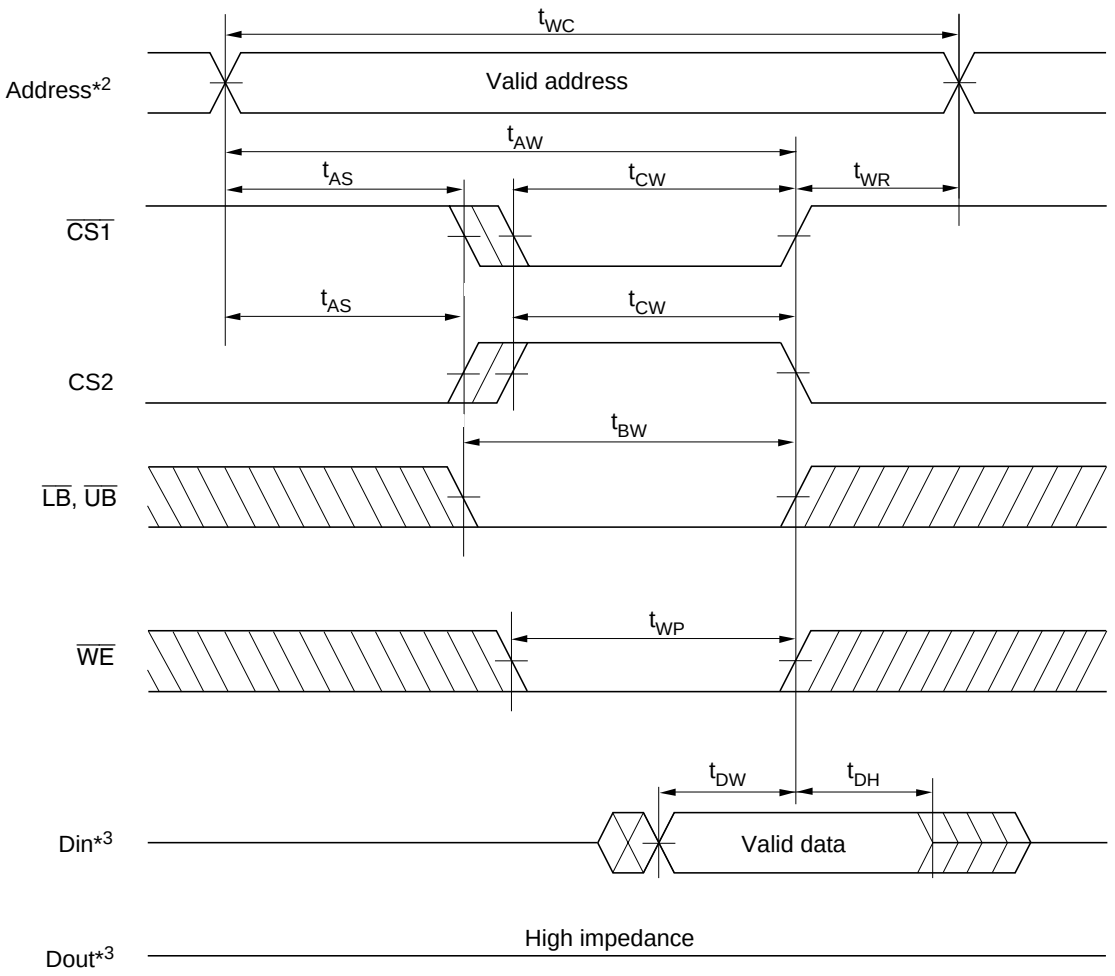
Notes: 1. Only for TSOP type.
$\overline{BYTE}$ > V_{CC} – 0.2 V or
$\overline{BYTE}$ < 0.2 V
2. Word mode: A0 to A19
Byte mode: A-1 to A19
3. Word mode: I/O0 to I/O15
Byte mode: I/O0 to I/O7

Write Cycle (1)*[1] ($\overline{WE}$ Clock)



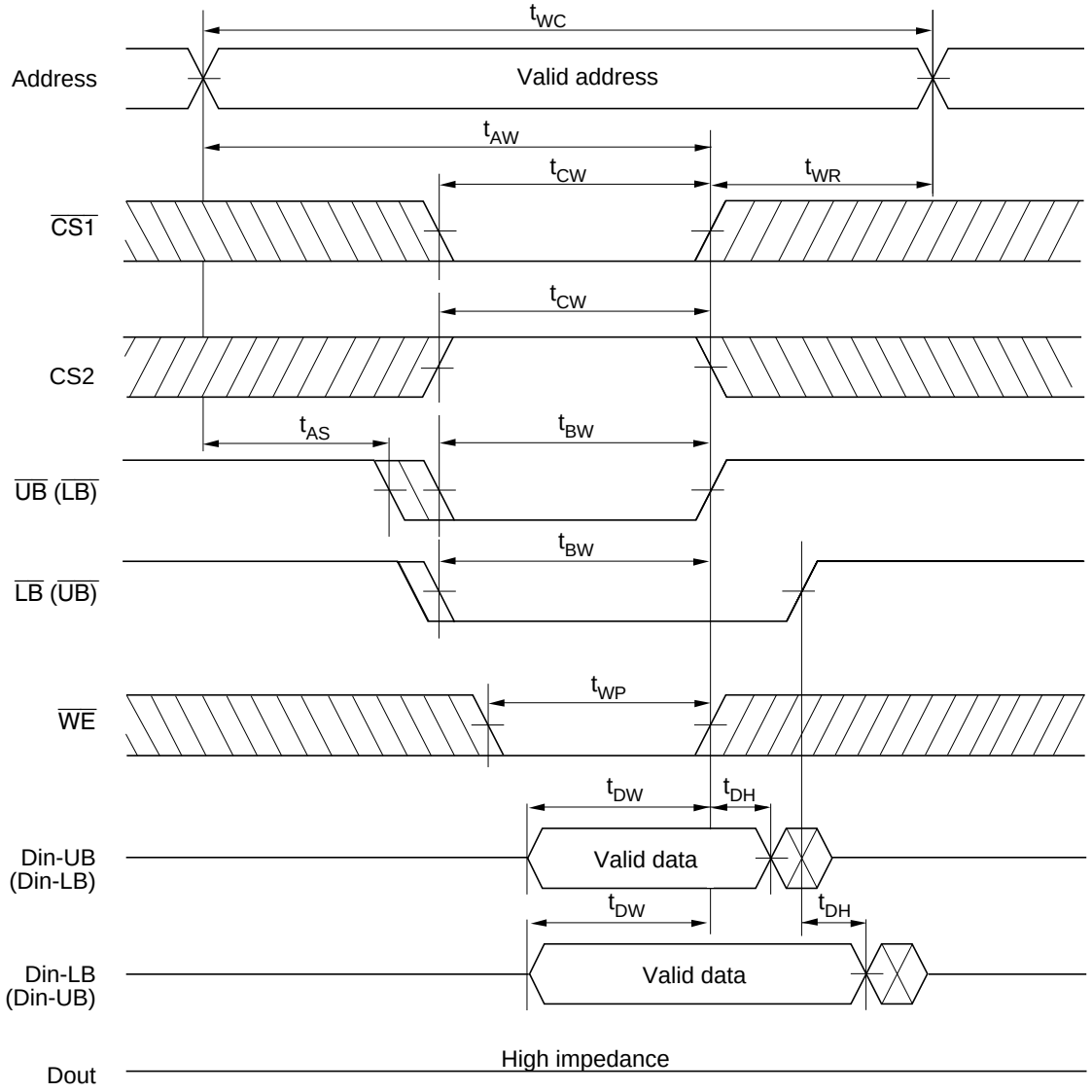
Notes: 1. Only for TSOP type.
$\overline{BYTE}$ > V_{CC} – 0.2 V or
$\overline{BYTE}$ < 0.2 V
2. Word mode: A0 to A19
Byte mode: A-1 to A19
3. Word mode: I/O0 to I/O15
Byte mode: I/O0 to I/O7

Write Cycle (2)*[1] ($\overline{CS1}$, CS2 Clock, $\overline{OE}$ = V_{IH})



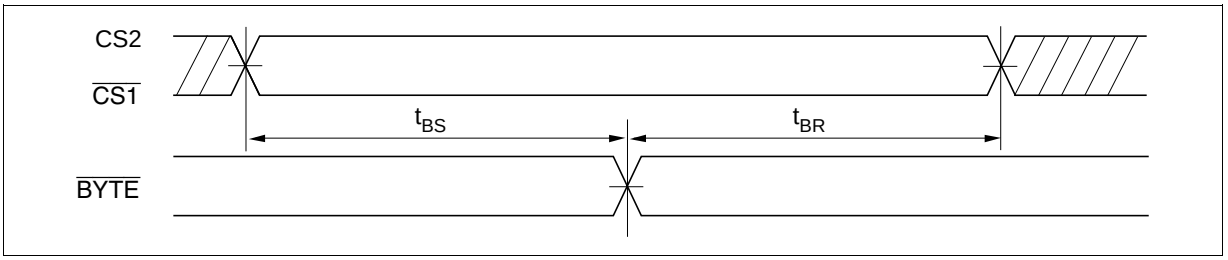
Notes: 1. Only for TSOP type.
$\overline{BYTE}$ > V_{CC} – 0.2 V or
$\overline{BYTE}$ < 0.2 V
2. Word mode: A0 to A19
Byte mode: A-1 to A19
3. Word mode: I/O0 to I/O15
Byte mode: I/O0 to I/O7

Write Cycle (3)*[1] ($\overline{LB}$, $\overline{UB}$ Clock, $\overline{OE}$ = V_{IH})



Note: 1. Only for TSOP type.
$\overline{BYTE}$ > V_{CC} – 0.2 V

Byte Control (TSOP)



Low V_{CC} Data Retention Characteristics (Ta = –40 to +85°C)

Parameter	Symbol	Min	Typ*[5]	Max	Unit	Test conditions*[3, 4]
V_{CC} for data retention	V_{DR}	1.5	—	3.6	V	Vin ≥ 0 V (1) 0 V ≤ CS2 ≤ 0.2 V or (2) CS2 ≥ V_{CC} – 0.2 V, $\overline{CS1}$ ≥ V_{CC} – 0.2 V or (3) $\overline{LB}$ = $\overline{UB}$ ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V, $\overline{CS1}$ ≤ 0.2 V
Data retention current	I_{CCDR}*[1]	—	0.5	25	µA	V_{CC} = 3.0 V, Vin ≥ 0 V (1) 0 V ≤ CS2 ≤ 0.2 V or (2) CS2 ≥ V_{CC} – 0.2 V, $\overline{CS1}$ ≥ V_{CC} – 0.2 V or (3) $\overline{LB}$ = $\overline{UB}$ ≥ V_{CC} – 0.2 V, CS2 ≥ V_{CC} – 0.2 V, $\overline{CS1}$ ≤ 0.2 V Average value
	I_{CCDR}*[2]	—	0.5	8	µA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveforms
Operation recovery time	t_R	5	—	—	ms	

Notes: 1. This characteristic is guaranteed only for L-version.

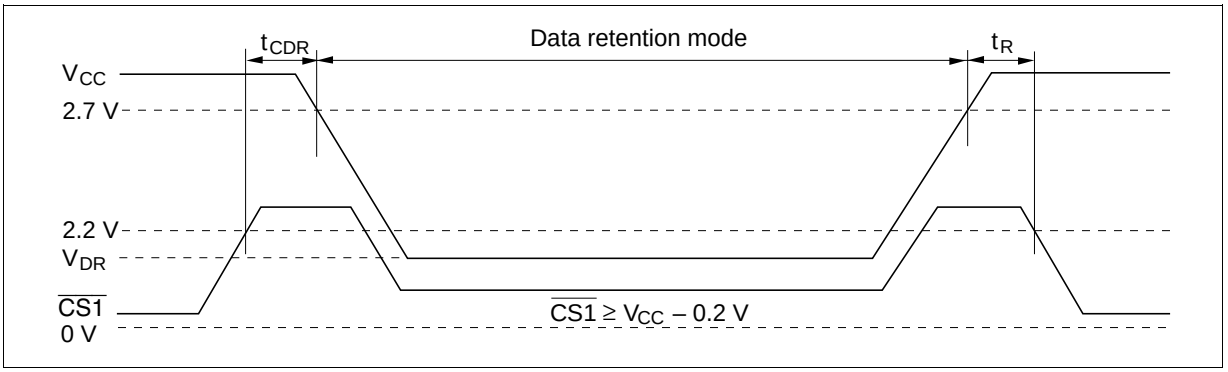
2. This characteristic is guaranteed only for L-SL version.

3. $\overline{BYTE}$ pin supported by only TSOP type.
   $\overline{BYTE}$ ≥ V_{CC} – 0.2 V or $\overline{BYTE}$ ≤ 0.2 V

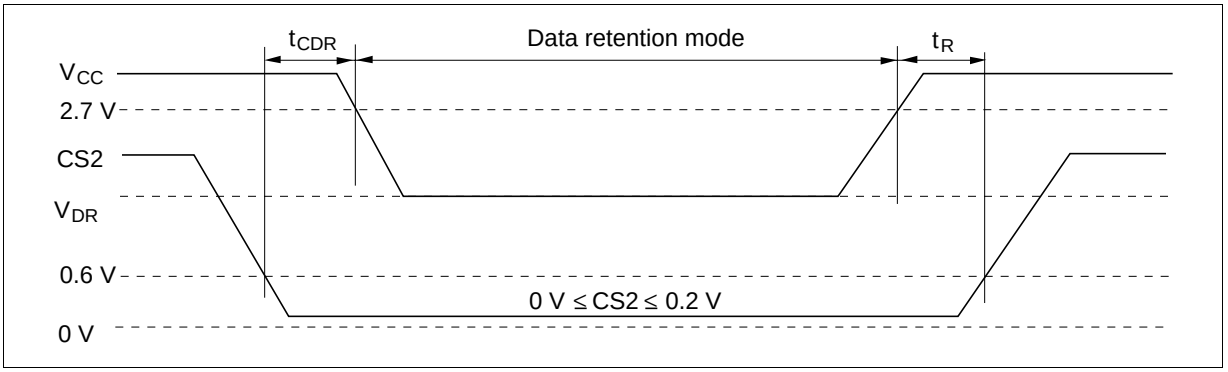
4. CS2 controls address buffer, $\overline{WE}$ buffer, $\overline{CS1}$ buffer, $\overline{OE}$ buffer, $\overline{LB}$, $\overline{UB}$ buffer and Din buffer. If CS2 controls data retention mode, Vin levels (address, $\overline{WE}$, $\overline{OE}$, $\overline{CS1}$, $\overline{LB}$, $\overline{UB}$, I/O) can be in the high impedance state. If $\overline{CS1}$ controls data retention mode, CS2 must be CS2 ≥ V_{CC} – 0.2 V or 0 V ≤ CS2 ≤ 0.2 V. The other input levels (address, $\overline{WE}$, $\overline{OE}$, $\overline{LB}$, $\overline{UB}$, I/O) can be in the high impedance state.

5. Typical values are at V_{CC} = 3.0 V, Ta = +25°C and not guaranteed.

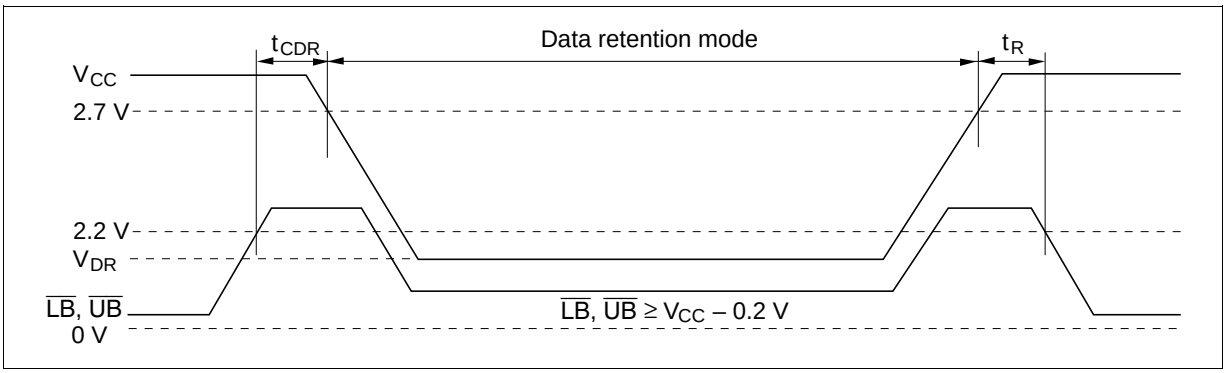
Low V_{CC} Data Retention Timing Waveform (1) ($\overline{CS1}$ Controlled)



Low V_{CC} Data Retention Timing Waveform (2) (CS2 Controlled)



Low V_{CC} Data Retention Timing Waveform (3) ($\overline{LB}$, $\overline{UB}$ Controlled)

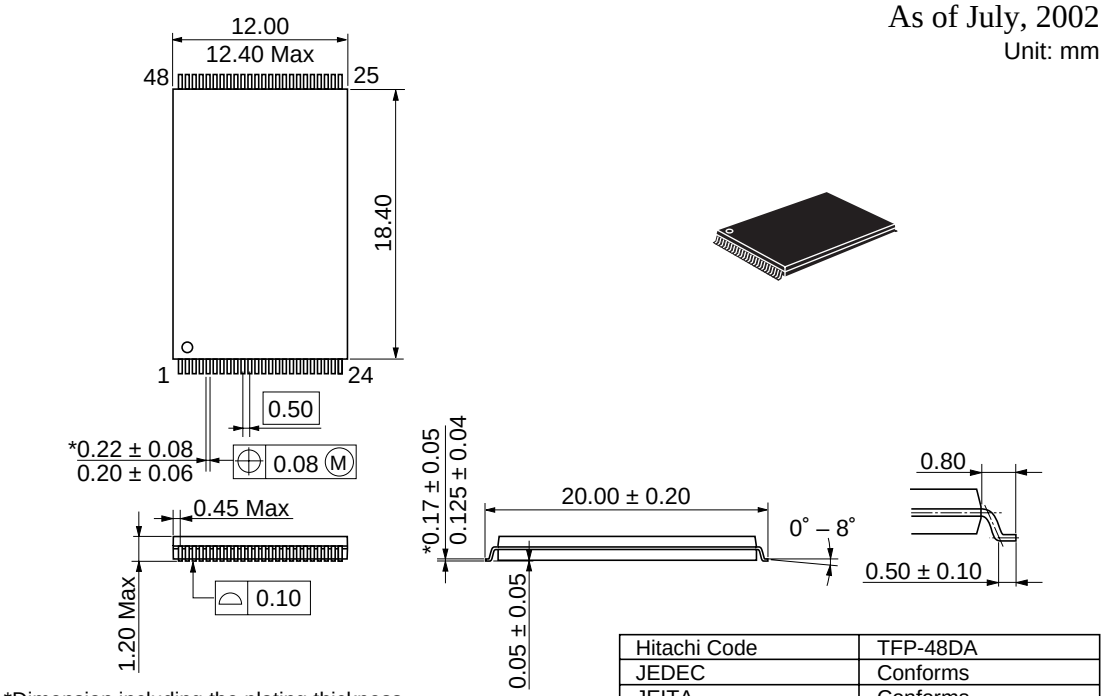


Package Dimensions

HM62V16100LTI Series (TFP-48DA)

As of July, 2002

Unit: mm



*Dimension including the plating thickness
Base material dimension

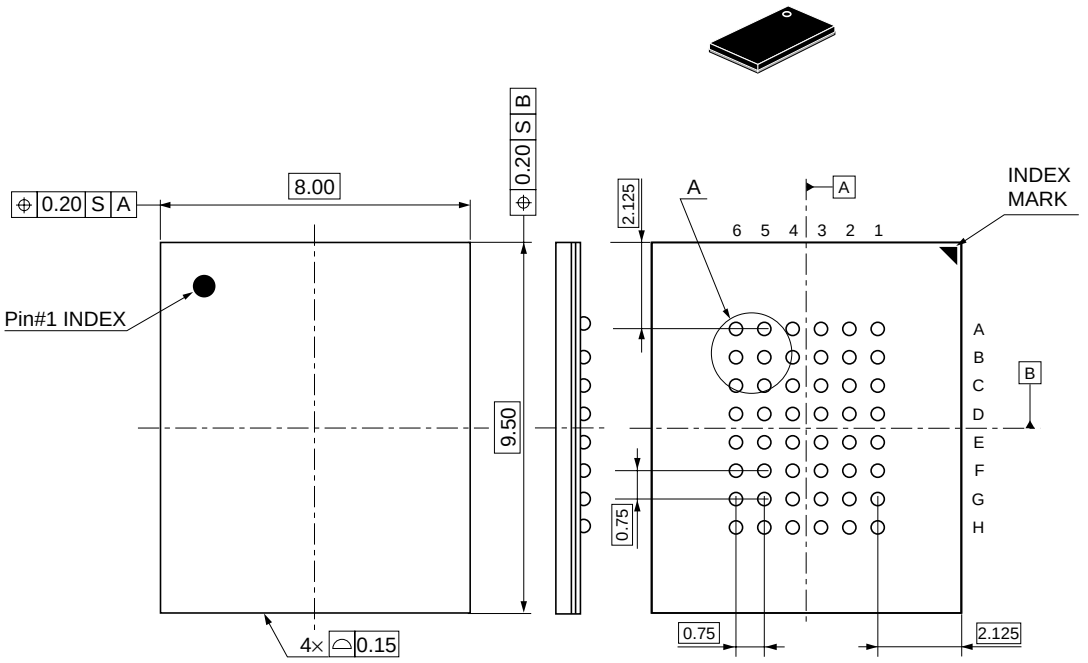
Hitachi Code	TFP-48DA
JEDEC	Conforms
JEITA	Conforms
Mass (reference value)	0.52 g

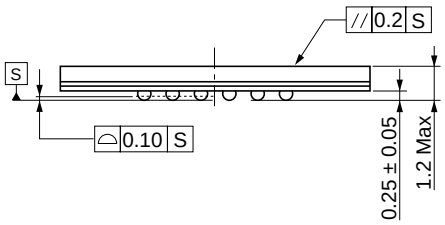
HM62V16100LBPI Series (TBP-48F)

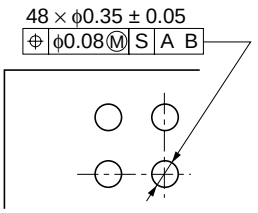
Preliminary

As of July, 2002

Unit: mm







Details of the part A

Hitachi Code	TBP-48F
JEDEC	–
JEITA	–
Mass (reference value)	0.15 g

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